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IN THE SPECIFICATION*Kindly replace paragraph 21 with the following replacement paragraph:*

--[0021] More preferably, the shortest distance X_1 from the pn-junction between the anode layer and the drift layer to the edge of the buffer layer on the side of the anode can be expressed by the following relational expression (2):

$$0.8 \leq X_1 / \{ (BV \epsilon_s) / q [(J_F / q v_{sat}) + N_D] \}^{1/2} \leq 1.2 \quad \dots(2),$$

where, BV is the breakdown voltage of the semiconductor device, ϵ_s is the dielectric permeability of the semiconductor, q is the elementary charge quantity, J_F is the rated current density of the semiconductor device, v_{sat} is the carrier saturation speed, and N_D is the concentration of the impurity of the first conductivity type in the drift layer. The thickness Y_1 of the buffer layer and the average impurity concentration N_{D2} of the buffer layer can be related with each other by the following relational expression (3):

$$Y_1 / \{ [X_1^2 + 2\epsilon_s (V_{CC} + V_{PT}) / q N_{D2}]^{1/2} + X_1 \} \leq 2 \quad \dots(3),$$

where X_1 is the shortest distance from the pn-junction between the anode layer and the drift layer to the edge of the buffer layer on the side of the anode, V_{CC} is the half value of the breakdown voltage of the semiconductor device, V_{PT} is the voltage, at which the depletion layer contacts the buffer layer of the first conductivity type, ϵ_s is the dielectric permeability of the semiconductor, and q is the elementary charge quantity.--